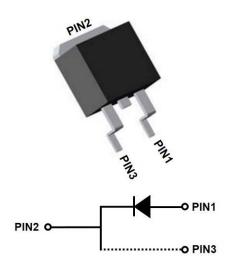






Silicon Carbide Schottky Diode

V_{RRM}	1200V
I _{F (135°C)}	23A
Q _C	104nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

Package: TO-263
 Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_c=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112020BXGH
Reverse voltage (Repetitive peak) @ T _j =25°C	V_{RRM}	٧	1200
Reverse voltage (Surge peak) @ T _j =25°C	V_{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V_{DC}	V	1200
Continuous forward current @ T _c =25°C			50
Continuous forward current @ T _C =135°C	I _F	Α	23
Continuous forward current @ T _C =145°C			20
Non-repetitive peak forward surge current @ T _C =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	145
Power Dissipation@ T _C =25°C	D	W	197
Power Dissipation@ T _C =110°C	P _{TOT}		85
i²t Value@ T _C =25°C ,tp=10ms	∫ i²dt	A ² S	105
Operating junction and Storage temperature range	T_j , T_stg	°C	-55 to +175





■Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.						
Forward voltage drop	V _F	V	I _F =20A, T _j =25°C	1.45	1.55						
			I _F =20A, T _j =175°C	2	-						
Povorce leakage current	I _R	μA	V _R =1200V, T _j =25°C	1	20						
Reverse leakage current			V _R =1200V, T _j =175°C	8	-						
Total capacitive charge	Q _C	nC	$\begin{array}{c} V_R {=} 800 V, \ T_j {=} 25^{\circ} C \ , \\ Q_C {=} \int_0^{VR} C(V) dV \end{array} \label{eq:VR}$	104	-						
	С								V _R =0V, f=1MHZ	1509	-
Total capacitance		pF	V _R =400V, f=1MHZ	98	-						
			V _R =800V, f=1MHZ	70	-						
Capacitance Stored Energy	Ec	μJ	V _R =800V	27	-						

■Thermal Characteristics $(T_a=25$ $^{\circ}$ C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{\theta J-C}$	°C W	0.76

■Typical Characteristics

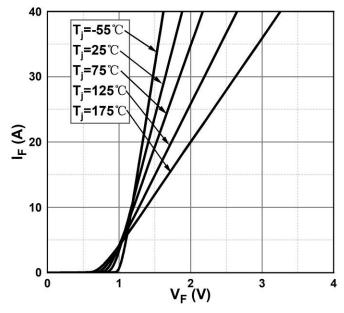


Figure 1. Forward Characteristics

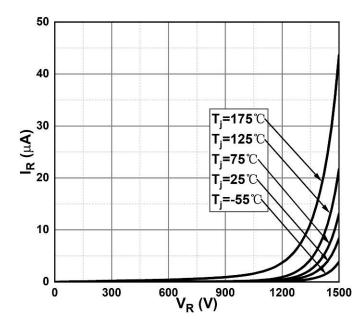
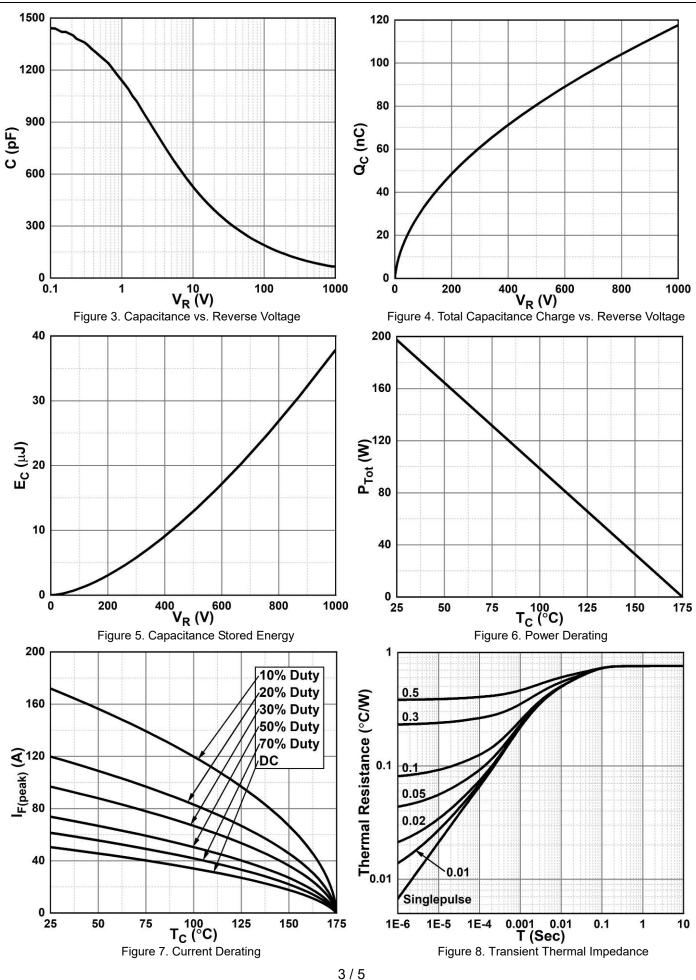


Figure 2. Reverse Characteristics

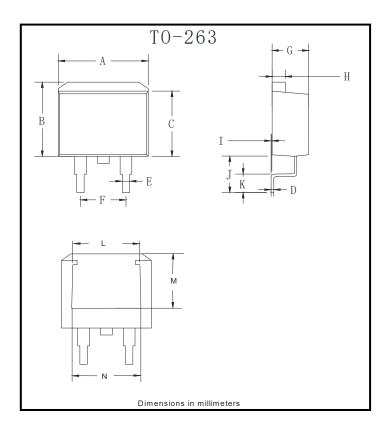








■Outline Dimensions



TO-263				
Dim	Min	Max		
Α	9.5	11.5		
В	9.7	10.5		
С	8.4	9.0		
D	0.28	0.64		
Е	0.68	0.94		
F	4.55	5.6		
G	4.04	5.10		
Н	1.14	1.4		
Ι	0	0.2		
J	4.9	6.05		
K	1.79	2.79		
L	7.3	7.9		
М	6.2	6.8		
N	7.6	8.2		



YJD112020BXGH



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